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IRF730B/IRFS730B

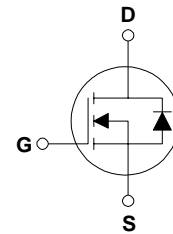
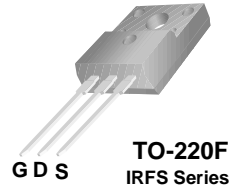
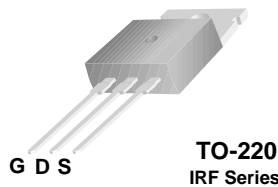
400V N-Channel MOSFET

General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supplies and electronic lamp ballasts based on half bridge.

Features

- 5.5A, 400V, $R_{DS(on)} = 1.0\Omega$ @ $V_{GS} = 10V$
- Low gate charge (typical 25 nC)
- Low Crss (typical 20 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	IRF730B	IRFS730B	Units
V _{DSS}	Drain-Source Voltage	400		V
I _D	Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C)	5.5	5.5 *	A
		3.5	3.5 *	A
I _{DM}	Drain Current - Pulsed (Note 1)	22	22 *	A
V _{GSS}	Gate-Source Voltage	± 30		V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	330		mJ
I _{AR}	Avalanche Current (Note 1)	5.5		A
E _{AR}	Repetitive Avalanche Energy (Note 1)	7.3		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5		V/ns
P _D	Power Dissipation (T _C = 25°C) - Derate above 25°C	73	38	W
		0.58	0.3	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150		°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		°C

* Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	IRF730B	IRFS730B	Units
R _{θJC}	Thermal Resistance, Junction-to-Case Max.	1.71	3.31	°C/W
R _{θCS}	Thermal Resistance, Case-to-Sink Typ.	0.5	--	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient Max.	62.5	62.5	°C/W

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	400	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.4	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	μA
		$V_{DS} = 320\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 2.75\text{ A}$	--	0.83	1.0	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 2.75\text{ A}$ (Note 4)	--	4.5	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	790	1000	pF
C_{oss}	Output Capacitance		--	80	100	pF
C_{riss}	Reverse Transfer Capacitance		--	20	26	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 200\text{ V}, I_D = 5.5\text{ A},$ $R_G = 25\ \Omega$	--	15	40	ns
t_r	Turn-On Rise Time		--	55	120	ns
$t_{d(off)}$	Turn-Off Delay Time		--	85	180	ns
t_f	Turn-Off Fall Time		(Note 4, 5)	--	50	110
Q_g	Total Gate Charge	$V_{DS} = 320\text{ V}, I_D = 5.5\text{ A},$ $V_{GS} = 10\text{ V}$	--	25	33	nC
Q_{gs}	Gate-Source Charge		--	4.3	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4, 5)	--	11	--

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	5.5	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	22	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 5.5\text{ A}$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 5.5\text{ A},$	--	265	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	2.32	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 19\text{mH}, I_{AS} = 5.5\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 5.5\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

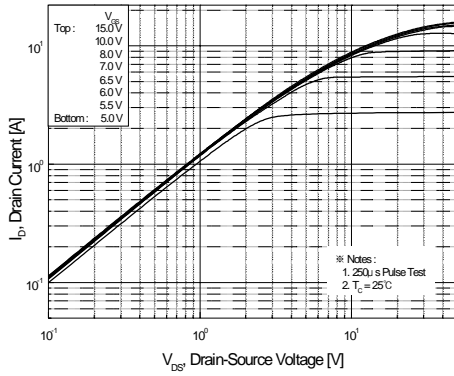


Figure 1. On-Region Characteristics

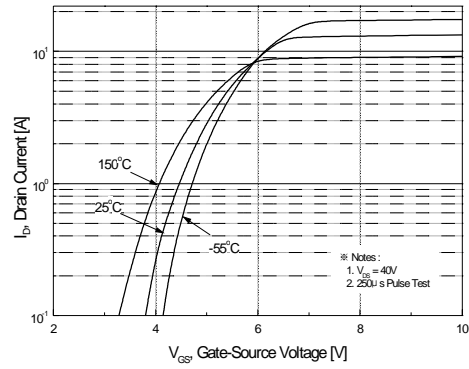


Figure 2. Transfer Characteristics

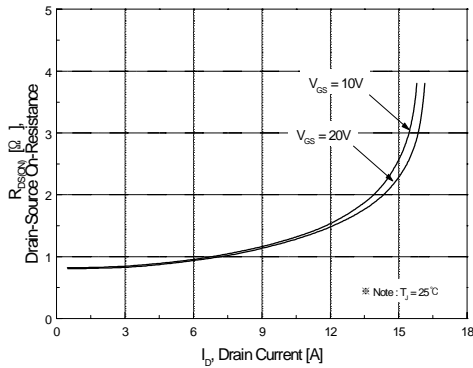


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

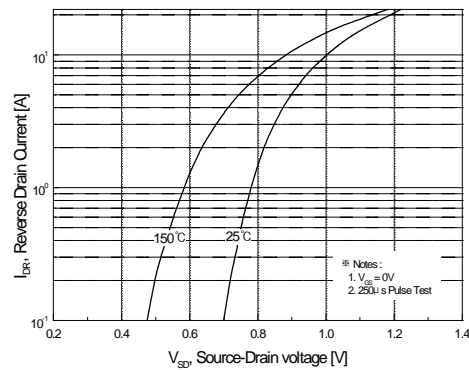


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

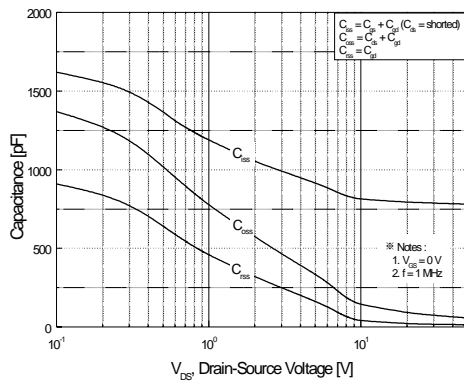


Figure 5. Capacitance Characteristics

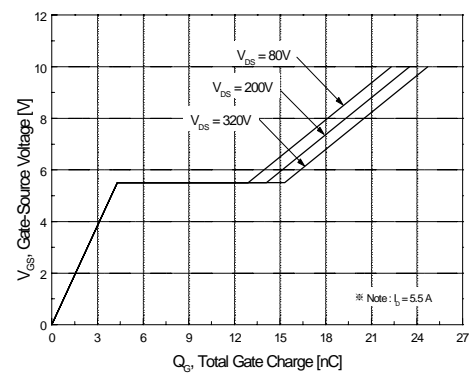


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

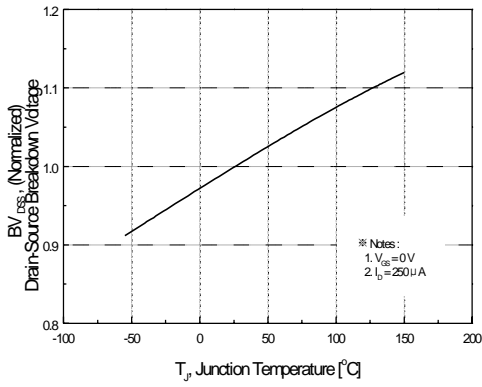


Figure 7. Breakdown Voltage Variation vs Temperature

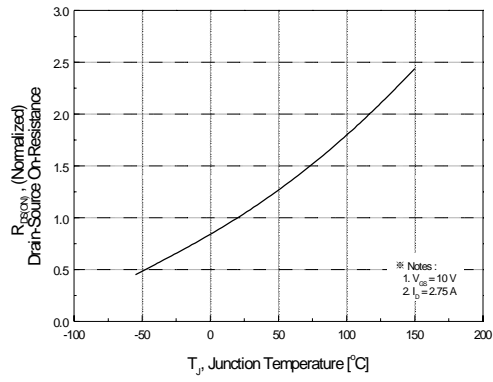


Figure 8. On-Resistance Variation vs Temperature

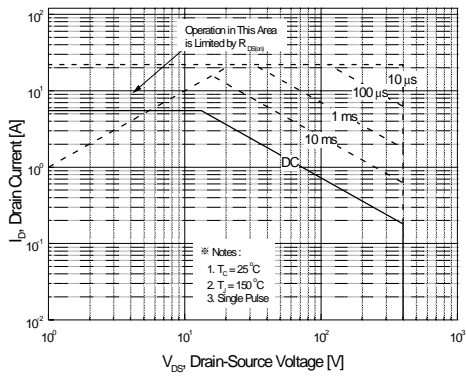


Figure 9-1. Maximum Safe Operating Area for IRF730B

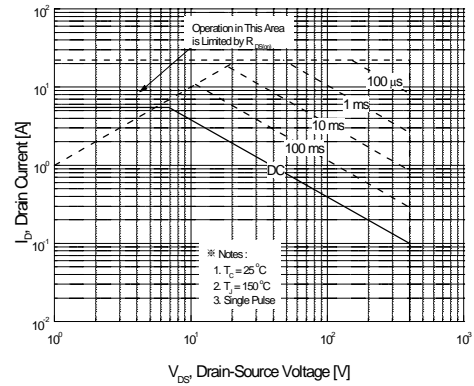


Figure 9-2. Maximum Safe Operating Area for IRFS730B

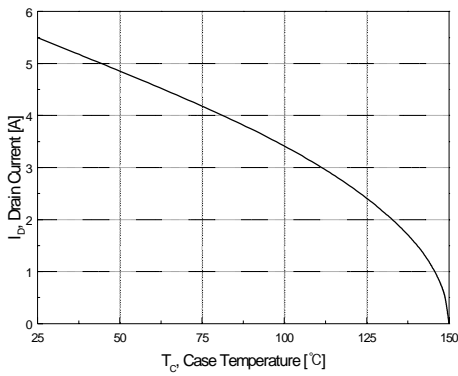


Figure 10. Maximum Drain Current vs Case Temperature



Typical Characteristics

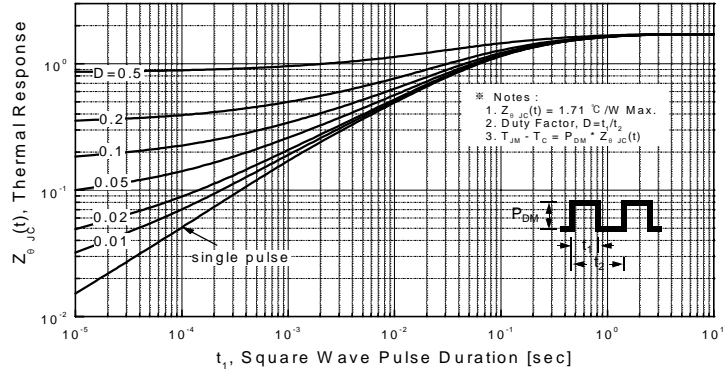


Figure 11. Transient Thermal Response Curve for IRF730B

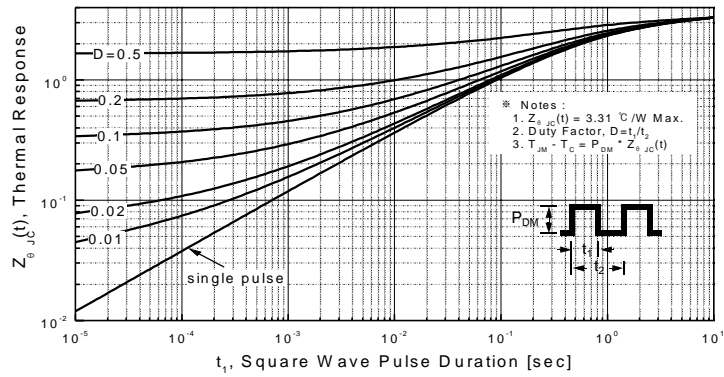
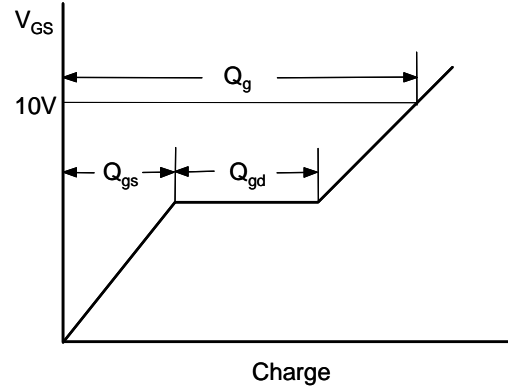
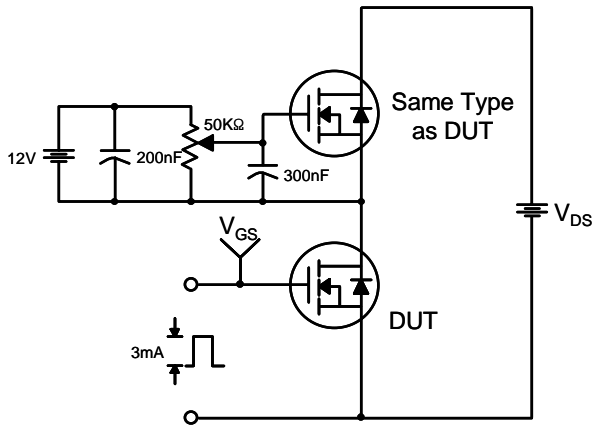


Figure 11-2. Transient Thermal Response Curve for IRFS730B

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

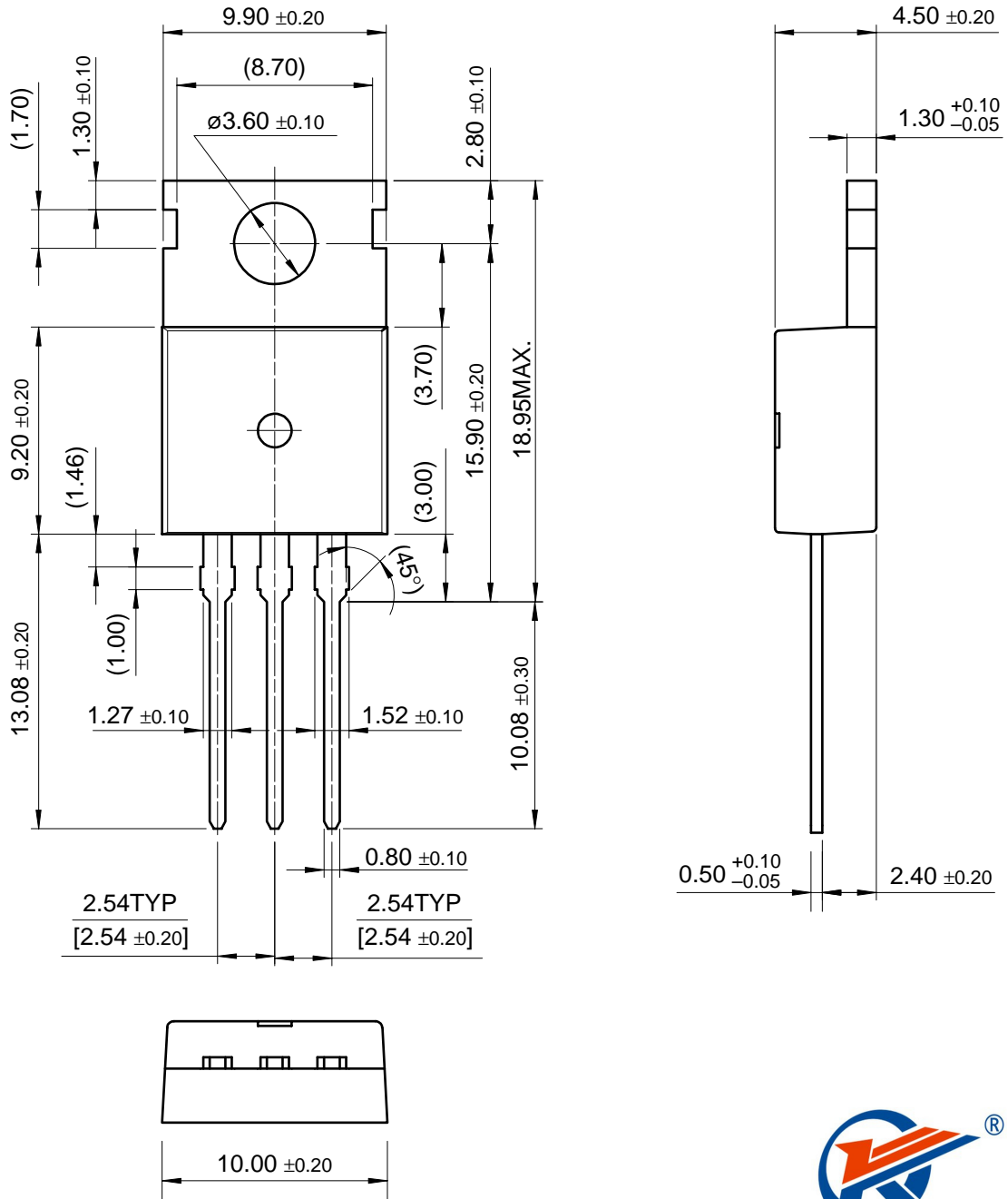


Unclamped Inductive Switching Test Circuit & Waveforms



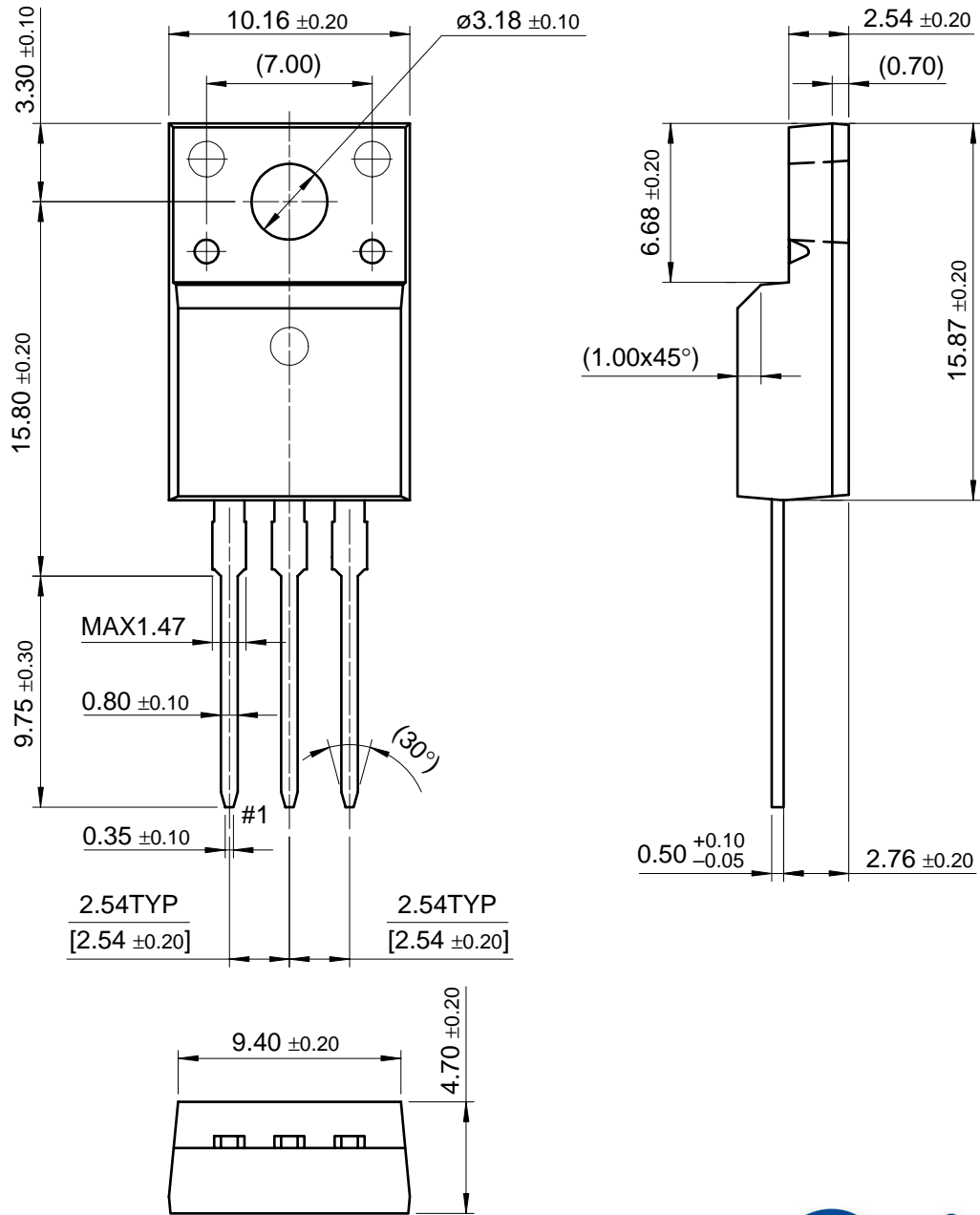
Package Dimensions

TO-220



Package Dimensions

TO-220F



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